

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max
20V	35mΩ @ V _{GS} = 10V	4.6A
	40mΩ @ V _{GS} = 4.5V	4.3A

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

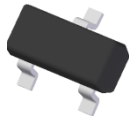
Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

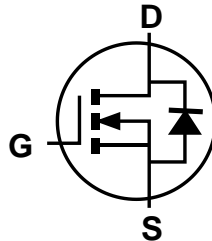
- Battery Charging
- Power Management Functions
- DC-DC Converters
- Portable Power Adaptors

Mechanical Data

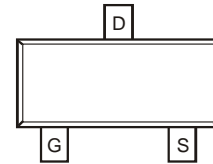
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)



Top View



Internal Schematic



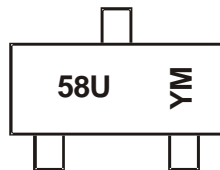
Top View

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2058U-7	SOT23	3,000/Tape & Reel
DMN2058U-13	SOT23	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



58U = Product Type Marking Code
 YM = Date Code Marking
 Y or \bar{Y} = Year (ex: D = 2016)
 M = Month (ex: 9 = September)

Date Code Key

Year	2016	2017	2018	2019	2020	2021	2022	2023
Code	D	E	F	G	H	I	J	K

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C	I _D	4.6	A
		T _A = +70°C		3.7	
Maximum Body Diode Forward Current (Note 6)			I _S	1.2	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	24	A

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Power Dissipation (Note 5)		P _D	0.74	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	172	°C/W
Power Dissipation (Note 6)		P _D	1.13	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	111	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	µA	V _{DS} = 20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±12V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.4	0.6	1.2	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	27	35	mΩ	V _{GS} = 10V, I _D = 6.0A
		—	30	40		V _{GS} = 4.5V, I _D = 5.0A
		—	37	60		V _{GS} = 2.5V, I _D = 4.0A
		—	49	91		V _{GS} = 1.8V, I _D = 2.0A
Diode Forward Voltage	V _{SD}	—	0.7	1.2	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{ISS}	—	281	—	pF	V _{DS} = 10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{OSS}	—	50	—		
Reverse Transfer Capacitance	C _{RSS}	—	39	—		
Gate Resistance	R _G	—	3.1	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _G	—	3.6	—	nC	V _{DS} = 10V, I _D = 6.0A
Total Gate Charge (V _{GS} = 10V)	Q _G	—	7.7	—		
Gate-Source Charge	Q _{GS}	—	0.5	—		
Gate-Drain Charge	Q _{GD}	—	0.9	—		
Turn-On Delay Time	t _{D(ON)}	—	2.0	—	ns	V _{GS} = 4.5V, V _{DD} = 10V, R _G = 6Ω, I _D = 6.0A
Turn-On Rise Time	t _r	—	4.9	—		
Turn-Off Delay Time	t _{D(OFF)}	—	9.9	—		
Turn-Off Fall Time	t _f	—	3.3	—		
Body Diode Reverse Recovery Time	t _{RR}	—	5.4	—	ns	I _F = 6.0A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q _{RR}	—	0.7	—	nC	I _F = 6.0A, di/dt = 100A/µs

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

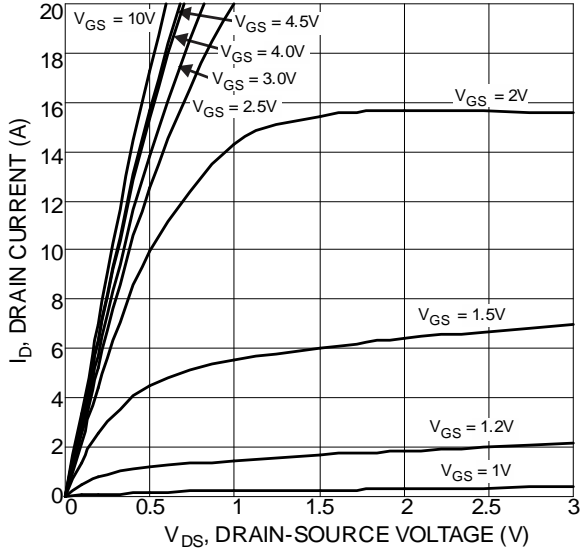


Figure 1 Typical Output Characteristic

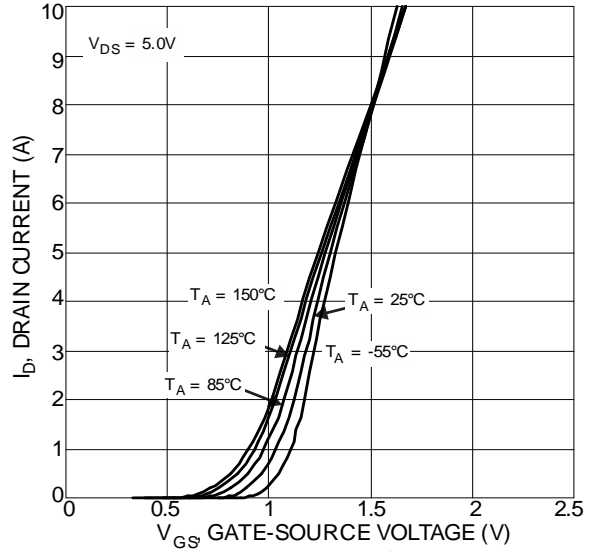


Figure 2 Typical Transfer Characteristics

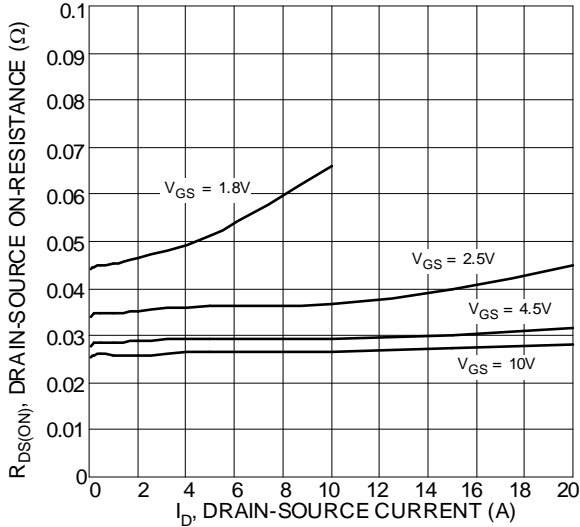


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

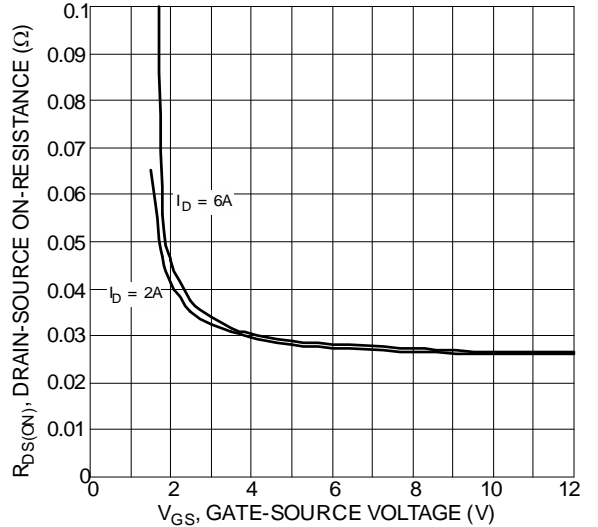


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

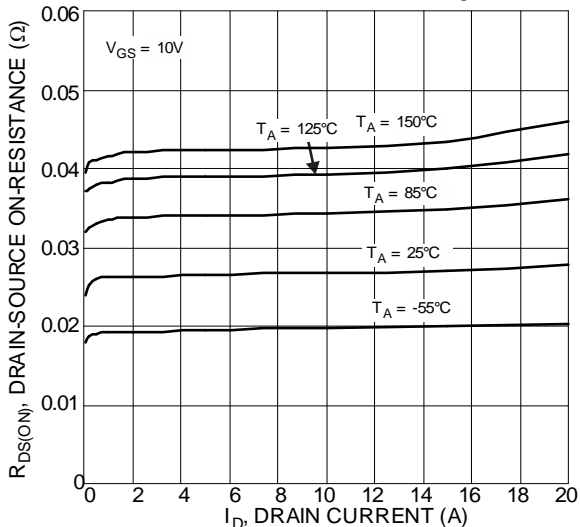


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

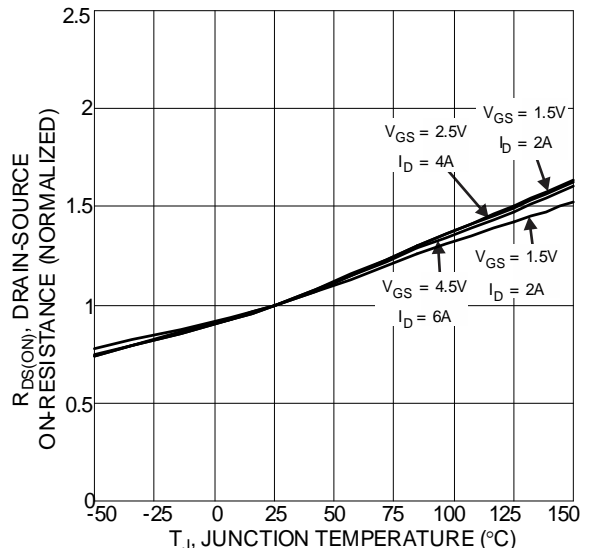


Figure 6 On-Resistance Variation with Temperature

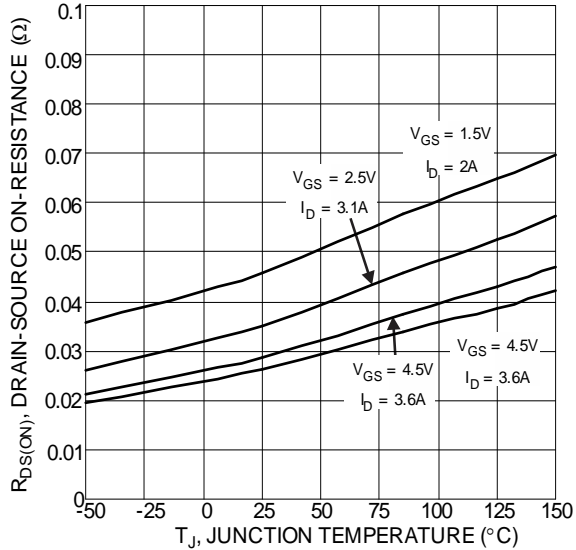


Figure 7 On-Resistance Variation with Temperature

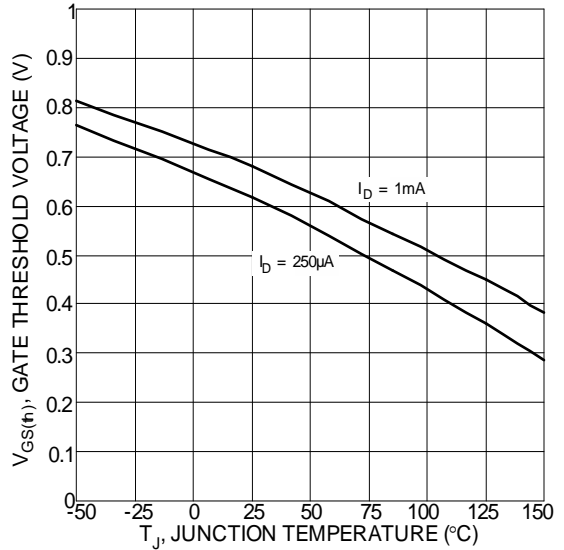


Figure 8 Gate Threshold Variation vs. Ambient Temperature

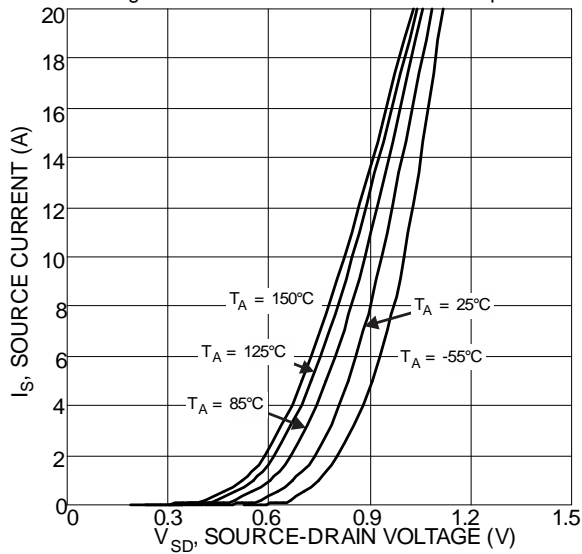


Figure 9 Diode Forward Voltage vs. Current

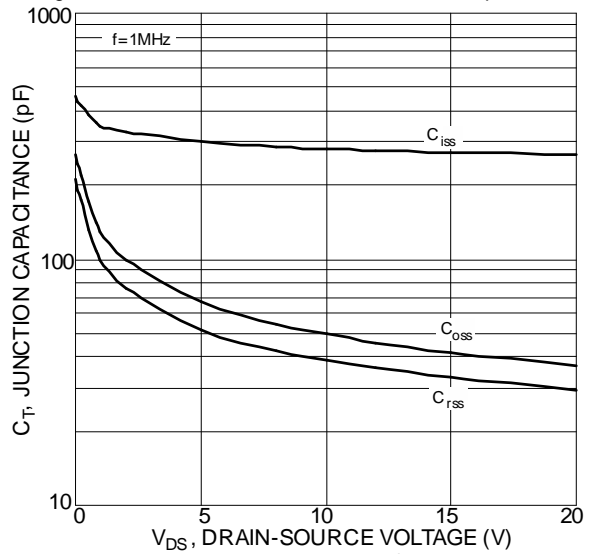


Figure 10 Typical Junction Capacitance

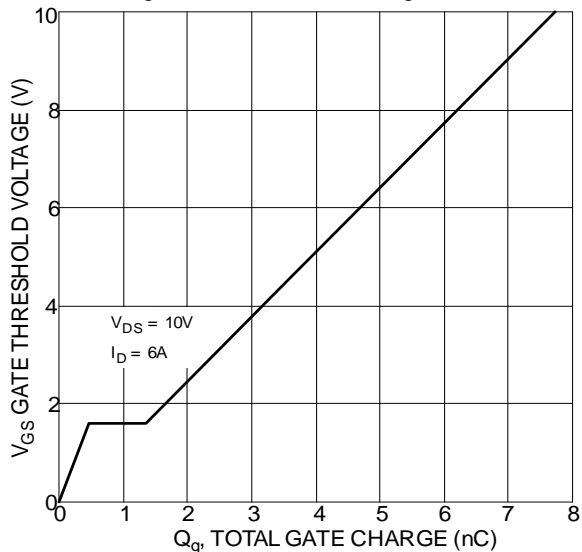


Figure 11 Gate Charge

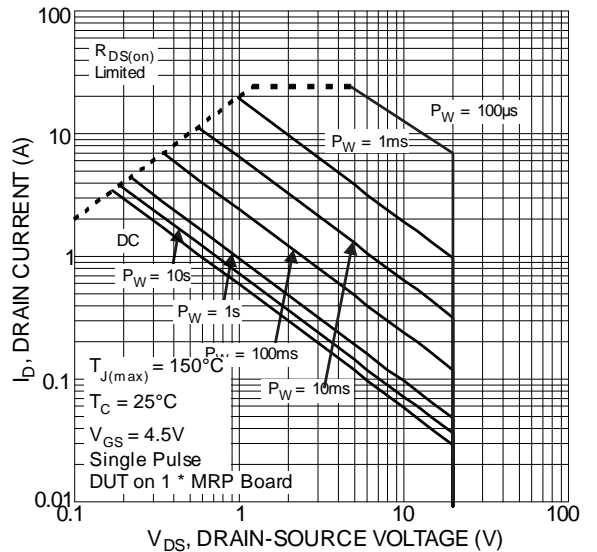
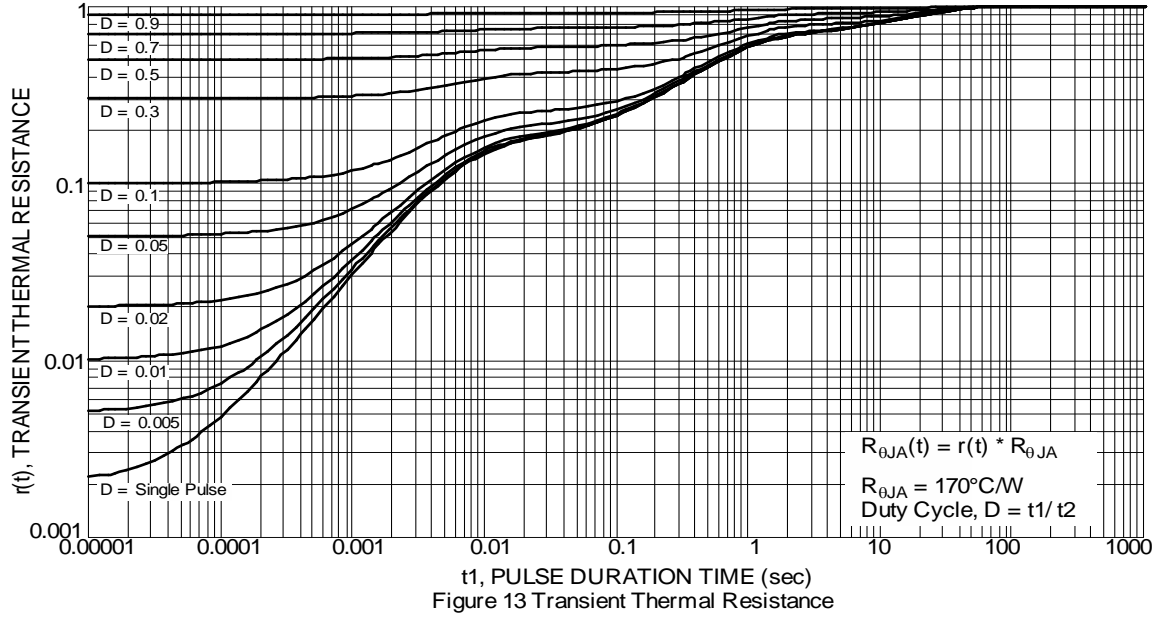


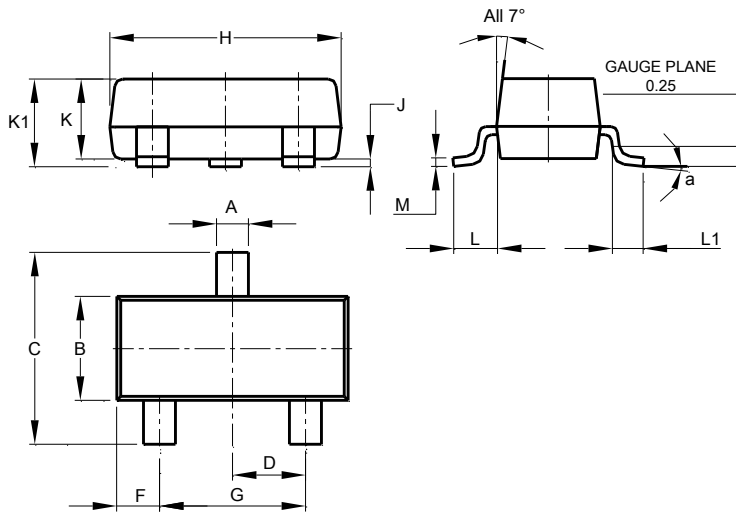
Figure 12 SOA, Safe Operation Area



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23

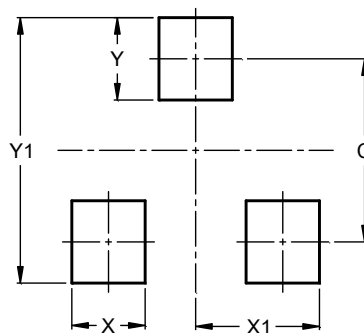


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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